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N-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY V_{DS} (V) $R_{DS(on)}$ (mΩ)(Typ.) I_D (A)a Q_g (Typ.) 40 15 at $V_{GS} = 10 \text{ V}$ 28 19.3 nC

FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- Low Gate Charge
- · RoHS and Halogen-Free Compliant

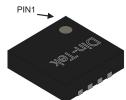
RoHS

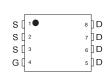
APPLICATIONS

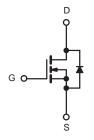
- · Load Switch
- PWM Application
- · Power Management

DFN3X3-8L Pin Configuration

Top View







N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	40	V	
Gate-Source Voltage		V _{GS}	± 20	V	
Continuous Drain Current (T _J = 175 °C) ^a	T _C = 25 °C	- I _D	28	А	
	T _C = 100 °C		21		
Pulsed Drain Current ^b		I _{DM}	112		
Single Avalanche Energy	E _{AS}	43	mJ		
Maximum Power Dissipation ^c	T _C = 25 °C	P _D	25	W	
	T _C = 100 °C		12.5		
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	LIMIT	UNIT	
Junction-to-Ambient (PCB Mount) ^d	R _{thJA}	62	°C/W	
Junction-to-Case (Drain)	R _{thJC}	6		

Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. $\,$ Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{0JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



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PARAMETER	T _C = 25 °C, unless otherwise noted) SYMBOL TEST CONDI		MIN.	TYP.	MAX.	UNIT	
Static							
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0 V, I _D = 250 μA	40	-	-	.,	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$ 1 -		3	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-	-	± 100	nA	
Zero Gate Voltage Drain Current		V _{DS} = 40 V, V _{GS} = 0 V	-	-	1		
	I _{DSS}	V _{DS} = 32 V, V _{GS} = 0 V, T _J = 55 °C		-	10	μΑ	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	28	-	-	Α	
		V _{GS} = 10 V, I _D = 10 A	-	15	18	mΩ	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 4.5 V, I _D = 8 A	-	17	22		
Forward Transconductance ^a	9fs	$V_{DS} = 5 \text{ V}, I_{D} = 10 \text{ A}$		67	-	S	
Dynamic ^b				<u>. </u>			
Input Capacitance	C _{iss}		-	939	-	pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 20 \text{ V}, f = 1 \text{ MHz}$	-	77	-		
Reverse Transfer Capacitance	C _{rss}		-	67	-		
Total Gate Charge ^c	Q_g		-	19.3	-		
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 20 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 10 \text{ A}$	-	1.8	-	nC	
Gate-Drain Charge ^c	Q_{gd}		-	3.25	-		
Gate Resistance	R_g	f = 1 MHz	-	4.6	-	Ω	
Turn-On Delay Time ^c	t _{d(on)}		-	12	-		
Rise Time ^c	t _r	$V_{DD} = 20 \text{ V}, I_D = 10 \text{ A}, R_g = 3 \Omega$	-	22	-	no	
Turn-Off Delay Time ^c	t _{d(off)}	$V_{GS} = 10 \text{ V}$, $R_L = 1 \Omega$	-	42	-	ns	
Fall Time ^c	t _f		-	15	-		
Drain-Source Body Diode Ratings and	Characterist	ics ^b (T _C = 25 °C)					
Continuous Source-Drain Diode Current	I _S	T _C = 25 °C	-	-	28	Α	
Pulsed Current	I _{SM}		-	-	112	Α	
Forward Voltage ^a	V_{SD}	I _F = 1 A, V _{GS} = 0 V	-	-	1.2	V	
Reverse Recovery Time	t _{rr}	I _F = 10 A, di/dt = 100 A/μs	-	15	-	ns	
Reverse Recovery Charge	Q _{rr}	η = 10 A, αι/αι - 100 A/μs	-	21	-	nC	

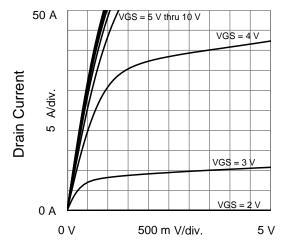
Notes

- a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

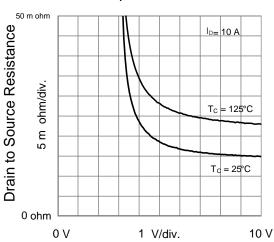
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those in dicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



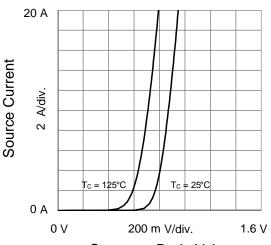
TYPICAL CHARAC TERISTICS (25 °C, unless otherwise noted)



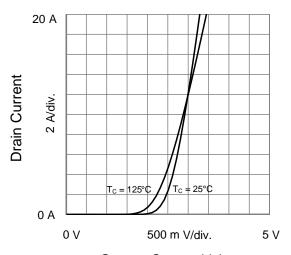
Drain to Source Voltage Output Characteristics



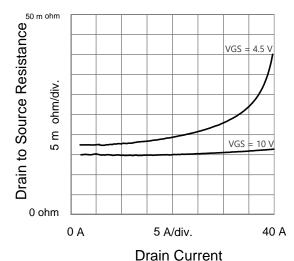
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltag



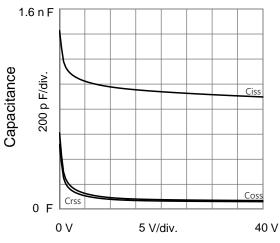
Source to Drain Voltage Body Diode Forward Characteristics



Gate to Source Voltage Transfer Characteristics



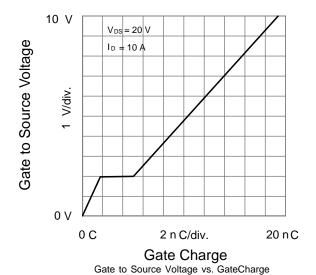
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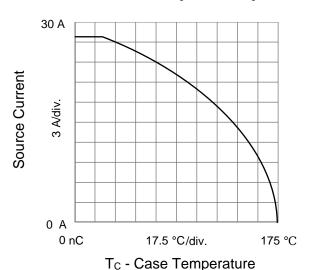


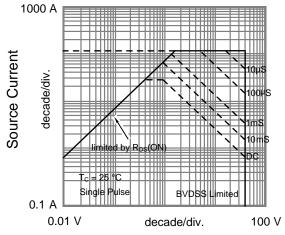
Drain to Source Voltage Capacitances



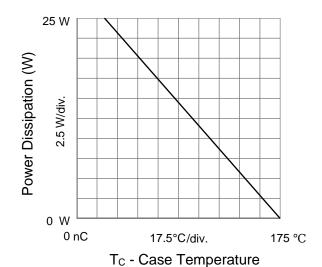
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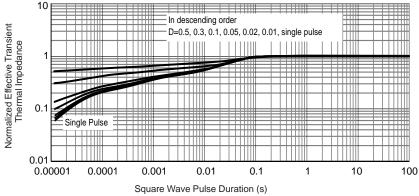






Source to Drain Voltage Safe Operating Area, Junction-to-Case

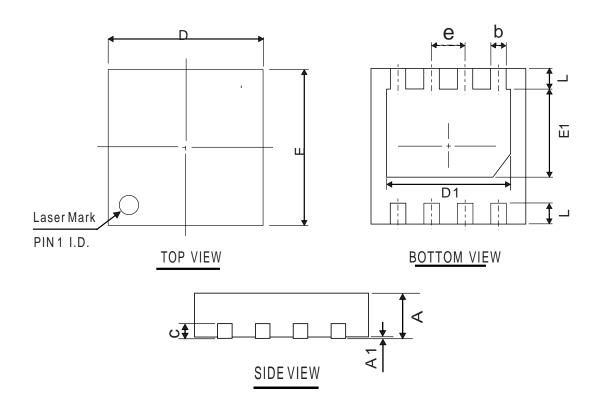




Normalized Thermal Transient Impedance, Junction-to-Case



DFN3*3-8L PACKAGEOUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
Α	0.60	0.75	0.90
A1	0.00	0.02	0.08
b	0.00	0.30	0.45
D	2.85	3.00	3.15
E	2.85	3.00	3.15
D1	2.10	2.40	2.70
E1	1.50	1.70	2.00
L	0.20	0.40	0.60
С	0.203REF		
е	0.65BSC		

OTHER DIMENSIONS

Α	0.50	0.55	0.60
Α	0.40	0.45	0.50





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